

Serial No. 10/089479

Filing Date
March 28, 2002

Group
2812

RECEIVED
SEP 16 2002
TECHNOLOGY CENTER 2800

[illegible][illegible]

✓		"Optical Process for Liftoff of Group III-Nitride Films", by Kelly et al., phys. stat. sol. (a) 159, R3 (1997)
✓		"Damage-free Separation of GaN Thin Films From Sapphire Substrates", by Wong et al., <u>Applied Physics Letters</u> , Vol. 72, No. 5, February 2, 1998, pages 599-601
✓		"Fabrication of Thin-Film InGaN Light-emitting Diode Membranes by Laser Lift-off", by Wong et al., <u>Applied Physics Letters</u> , Vol. 75, No. 10, September 6, 1999, pages 1360-1362
✓		"Large Free-Standing GaN Substrates by Hydride Vapor Phase Epitaxy and Laser-Induced Liftoff", by Kelly et al., <u>Jpn. J. Appl. Phys.</u> , Vol. 38 (1999) pages L217-L219

Examiner

Date Considered

3/30/03

* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.